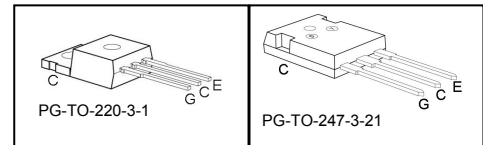
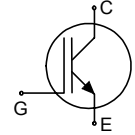


## Low Loss IGBT in TrenchStop® and Fieldstop technology

- Very low  $V_{CE(sat)}$  1.5 V (typ.)
- Maximum Junction Temperature 175 °C
- Short circuit withstand time – 5µs
- Designed for :
  - Frequency Converters
  - Uninterrupted Power Supply
- TrenchStop® and Fieldstop technology for 600 V applications offers :
  - very tight parameter distribution
  - high ruggedness, temperature stable behavior
  - very high switching speed
  - low  $V_{CE(sat)}$
- Positive temperature coefficient in  $V_{CE(sat)}$
- Low EMI
- Low Gate Charge
- Qualified according to JEDEC<sup>1</sup> for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models : <http://www.infineon.com/igbt/>



Type	$V_{CE}$	$I_C$	$V_{CE(sat), T_j=25^\circ C}$	$T_{j,max}$	Marking	Package
IGP50N60T	600 V	50 A	1.5 V	175 °C	G50T60	PG-TO-220-3-1
IGW50N60T	600 V	50 A	1.5 V	175 °C	G50T60	PG-TO-247-3-21

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CE}$	600	V
DC collector current, limited by $T_{j,max}$	$I_C$	100	A
$T_C = 25^\circ C$		100	
$T_C = 100^\circ C$		50	
Pulsed collector current, $t_p$ limited by $T_{j,max}$	$I_{C,puls}$	150	
Turn off safe operating area ( $V_{CE} \leq 600V, T_j \leq 175^\circ C$ )	-	150	
Gate-emitter voltage	$V_{GE}$	$\pm 20$	V
Short circuit withstand time <sup>2)</sup>	$t_{SC}$	5	µs
$V_{GE} = 15V, V_{CC} \leq 400V, T_j \leq 150^\circ C$			
Power dissipation $T_C = 25^\circ C$	$P_{tot}$	333	W
Operating junction temperature	$T_j$	-40...+175	°C
Storage temperature	$T_{stg}$	-55...+175	
Soldering temperature, 1.6mm (0.063 in.) from case for 10s	-	260	

<sup>1</sup> J-STD-020 and JESD-022

<sup>2)</sup> Allowed number of short circuits: <1000; time between short circuits: >1s.

**Thermal Resistance**

Parameter	Symbol	Conditions	Max. Value	Unit
<b>Characteristic</b>				
IGBT thermal resistance, junction – case	$R_{thJC}$		0.45	K/W
Thermal resistance, junction – ambient	$R_{thJA}$	PG-TO-220-3-1 PG-TO-247-3-21	62 40	

**Electrical Characteristic, at  $T_j = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
<b>Static Characteristic</b>						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=0.2mA$	600	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C=50A$ $T_j=25^\circ\text{C}$ $T_j=175^\circ\text{C}$	- -	1.5 1.9	2.0 -	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=0.8mA, V_{CE}=V_{GE}$	4.1	4.9	5.7	
Zero gate voltage collector current	$I_{CES}$	$V_{CE}=600V,$ $V_{GE}=0V$ $T_j=25^\circ\text{C}$ $T_j=175^\circ\text{C}$	- -	- -	40 1000	$\mu\text{A}$
Gate-emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V$	-	-	100	nA
Transconductance	$g_{fs}$	$V_{CE}=20V, I_C=50A$	-	31	-	S
Integrated gate resistor	$R_{Gint}$		-			$\Omega$

**Dynamic Characteristic**

Input capacitance	$C_{iss}$	$V_{CE}=25V,$	-	3140	-	pF
Output capacitance	$C_{oss}$	$V_{GE}=0V,$	-	200	-	
Reverse transfer capacitance	$C_{rss}$	$f=1MHz$	-	93	-	
Gate charge	$Q_{Gate}$	$V_{CC}=480V, I_C=50A$ $V_{GE}=15V$	-	310	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	$L_E$	PG-TO-220-3-1 PG-TO-247-3-21	- -	7 13	- -	nH
Short circuit collector current <sup>1)</sup>	$I_{C(SC)}$	$V_{GE}=15V, t_{SC}\leq 5\mu s$ $V_{CC} = 400V,$ $T_j \leq 150^\circ\text{C}$	-	458.3	-	A

<sup>1)</sup> Allowed number of short circuits: <1000; time between short circuits: >1s.

**Switching Characteristic, Inductive Load, at  $T_j=25^\circ\text{C}$** 

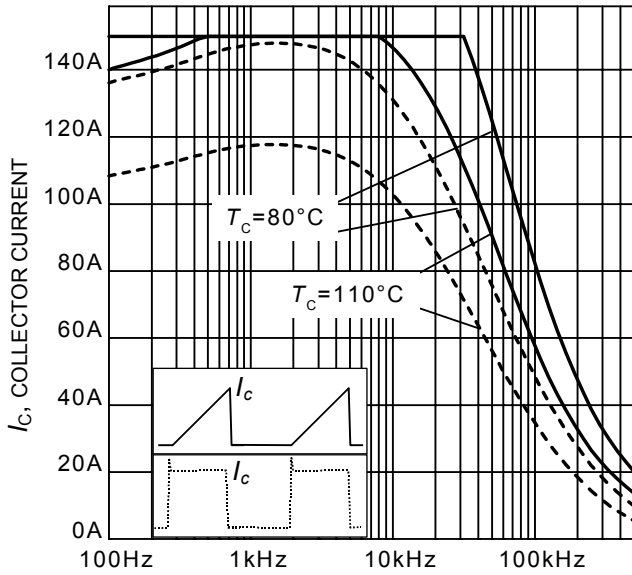
Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
<b>IGBT Characteristic</b>						
Turn-on delay time	$t_{d(\text{on})}$	$T_j=25^\circ\text{C}$ , $V_{\text{CC}}=400\text{V}$ , $I_{\text{C}}=50\text{A}$ , $V_{\text{GE}}=0/15\text{V}$ , $R_{\text{G}}=7\ \Omega$ , $L_{\sigma}^{(1)}=103\text{nH}$ , $C_{\sigma}^{(1)}=39\text{pF}$ Energy losses include "tail" and diode reverse recovery. <sup>2)</sup>	-	26	-	ns
Rise time	$t_{\text{r}}$		-	29	-	
Turn-off delay time	$t_{d(\text{off})}$		-	299	-	
Fall time	$t_{\text{f}}$		-	29	-	
Turn-on energy	$E_{\text{on}}$		-	1.2	-	mJ
Turn-off energy	$E_{\text{off}}$		-	1.4	-	
Total switching energy	$E_{\text{ts}}$		-	2.6	-	

**Switching Characteristic, Inductive Load, at  $T_j=150^\circ\text{C}$** 

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
<b>IGBT Characteristic</b>						
Turn-on delay time	$t_{d(\text{on})}$	$T_j=175^\circ\text{C}$ , $V_{\text{CC}}=400\text{V}$ , $I_{\text{C}}=50\text{A}$ , $V_{\text{GE}}=0/15\text{V}$ , $R_{\text{G}}=7\ \Omega$ , $L_{\sigma}^{(1)}=103\text{nH}$ , $C_{\sigma}^{(1)}=39\text{pF}$ Energy losses include "tail" and diode reverse recovery. <sup>2)</sup>	-	27	-	ns
Rise time	$t_{\text{r}}$		-	33	-	
Turn-off delay time	$t_{d(\text{off})}$		-	341	-	
Fall time	$t_{\text{f}}$		-	55	-	
Turn-on energy	$E_{\text{on}}$		-	1.8	-	mJ
Turn-off energy	$E_{\text{off}}$		-	1.8	-	
Total switching energy	$E_{\text{ts}}$		-	3.6	-	

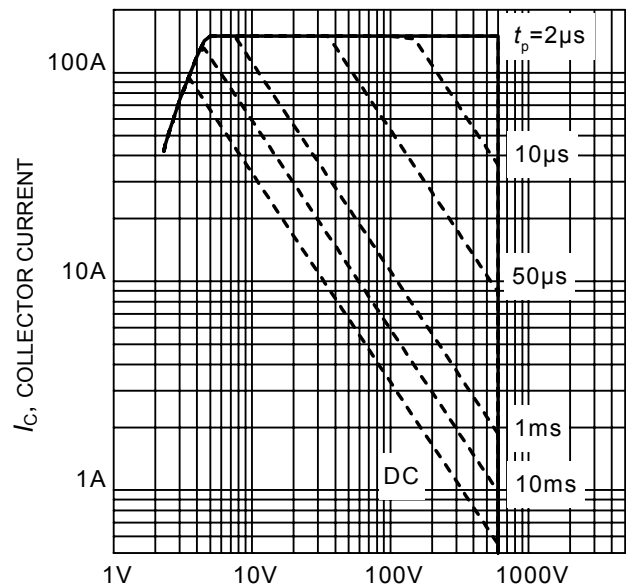
<sup>1)</sup> Leakage inductance  $L_{\sigma}$  and Stray capacity  $C_{\sigma}$  due to dynamic test circuit in Figure E.

<sup>2)</sup> Includes Reverse Recovery Losses from IKW50N60T due to dynamic test circuit in Figure E.



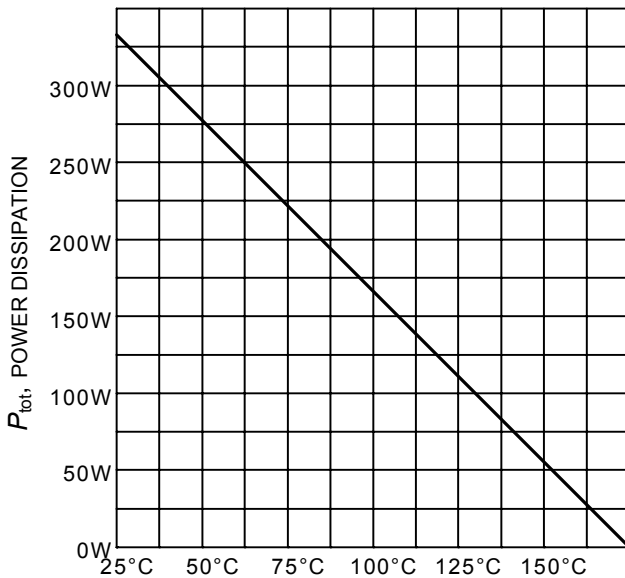
$f$ , SWITCHING FREQUENCY

**Figure 1. Collector current as a function of switching frequency**  
( $T_j \leq 175^\circ\text{C}$ ,  $D = 0.5$ ,  $V_{CE} = 400\text{V}$ ,  
 $V_{GE} = 0/+15\text{V}$ ,  $R_G = 7\Omega$ )



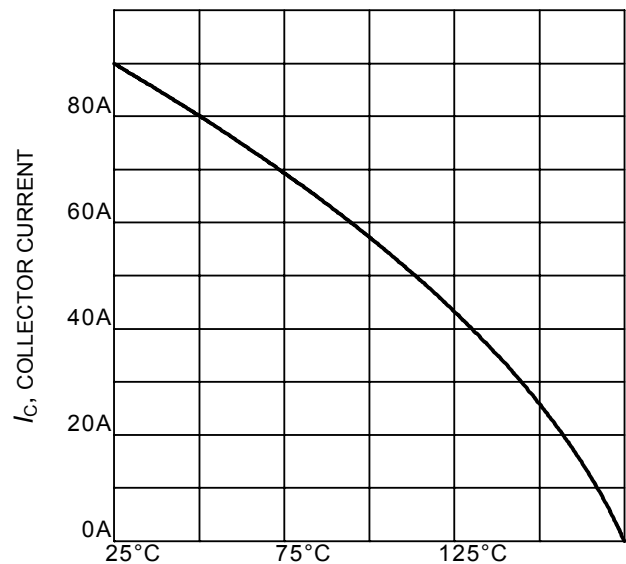
$V_{CE}$ , COLLECTOR-EMITTER VOLTAGE

**Figure 2. Safe operating area**  
( $D = 0$ ,  $T_C = 25^\circ\text{C}$ ,  $T_j \leq 175^\circ\text{C}$ ;  
 $V_{GE} = 15\text{V}$ )



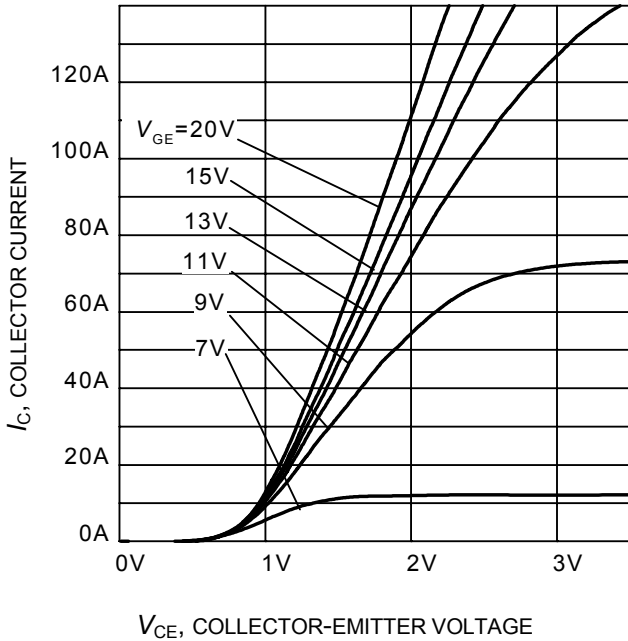
$T_C$ , CASE TEMPERATURE

**Figure 3. Power dissipation as a function of case temperature**  
( $T_j \leq 175^\circ\text{C}$ )

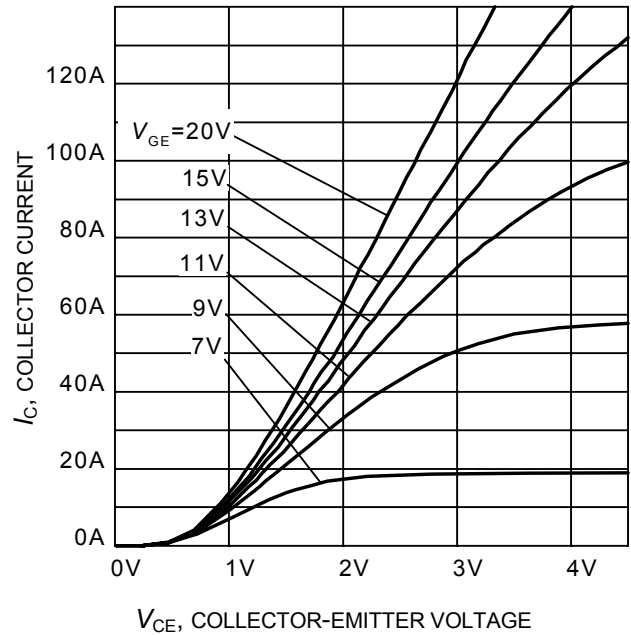


$T_C$ , CASE TEMPERATURE

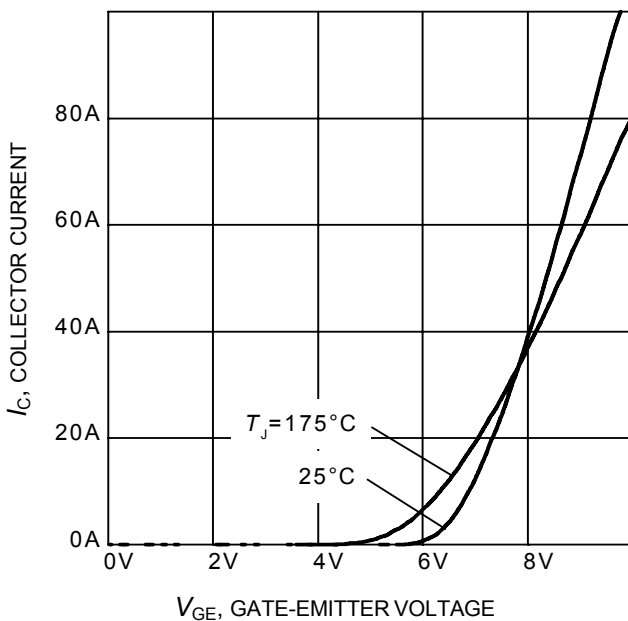
**Figure 4. Collector current as a function of case temperature**  
( $V_{GE} \geq 15\text{V}$ ,  $T_j \leq 175^\circ\text{C}$ )



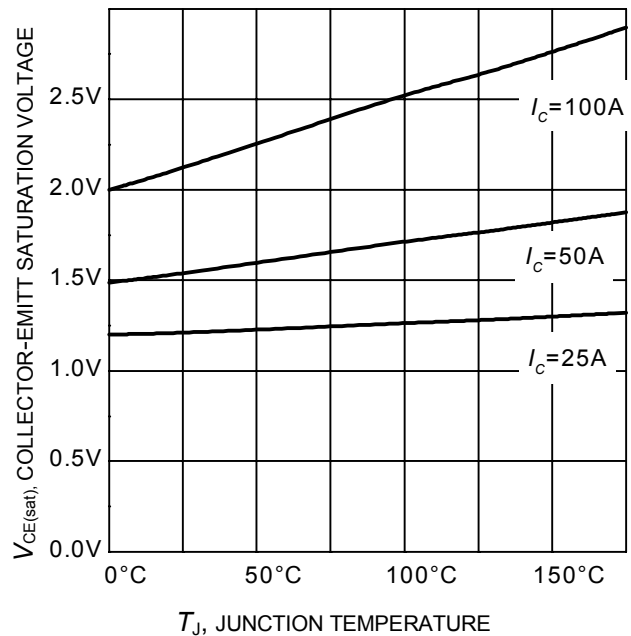
**Figure 5. Typical output characteristic**  
( $T_j = 25^\circ\text{C}$ )



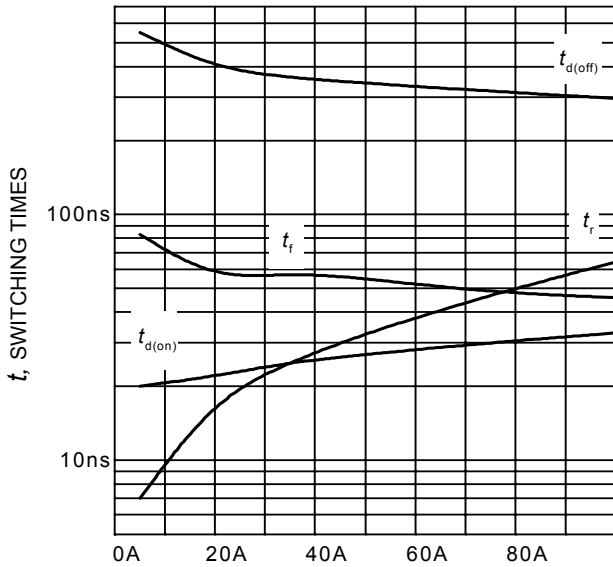
**Figure 6. Typical output characteristic**  
( $T_j = 175^\circ\text{C}$ )



**Figure 7. Typical transfer characteristic**  
( $V_{CE} = 20\text{V}$ )

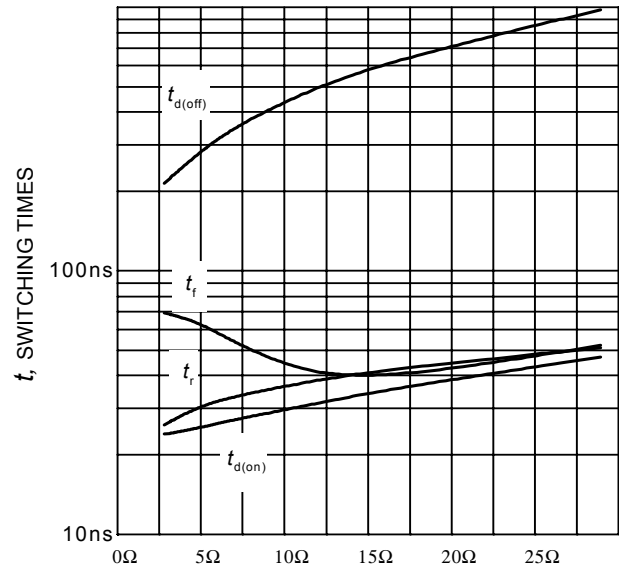


**Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature**  
( $V_{GE} = 15\text{V}$ )



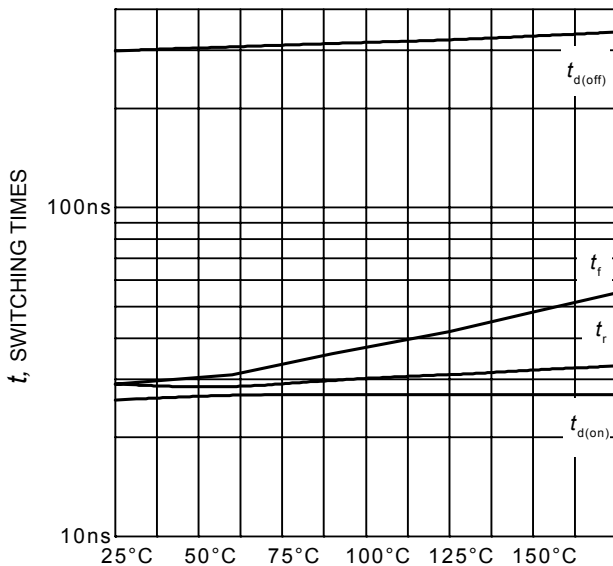
$I_C$ , COLLECTOR CURRENT

**Figure 9. Typical switching times as a function of collector current**  
(inductive load,  $T_J=175^\circ\text{C}$ ,  $V_{CE} = 400\text{V}$ ,  $V_{GE} = 0/15\text{V}$ ,  $R_G = 7\Omega$ , Dynamic test circuit in Figure E)



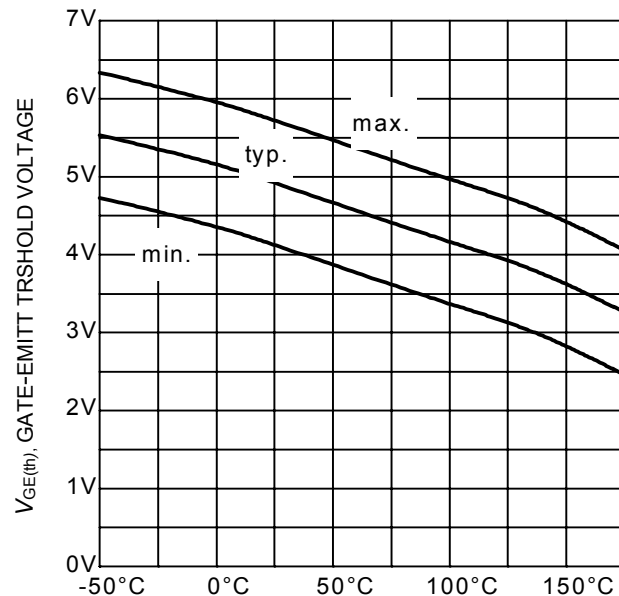
$R_G$ , GATE RESISTOR

**Figure 10. Typical switching times as a function of gate resistor**  
(inductive load,  $T_J = 175^\circ\text{C}$ ,  $V_{CE} = 400\text{V}$ ,  $V_{GE} = 0/15\text{V}$ ,  $I_C = 50\text{A}$ , Dynamic test circuit in Figure E)



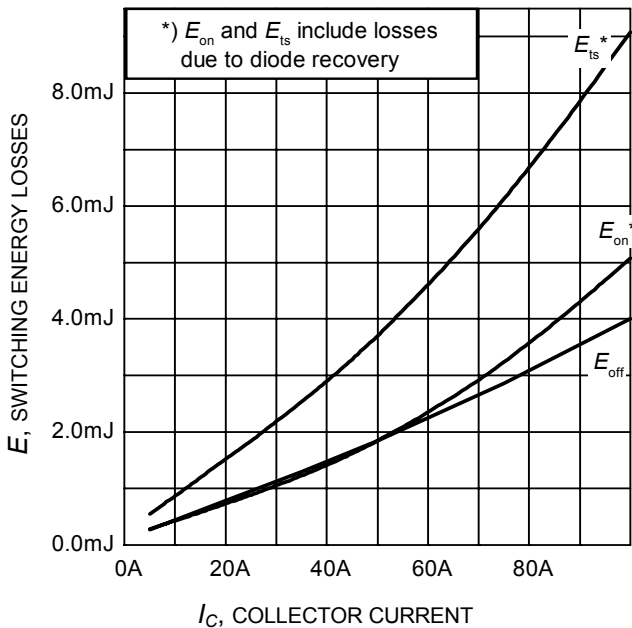
$T_J$ , JUNCTION TEMPERATURE

**Figure 11. Typical switching times as a function of junction temperature**  
(inductive load,  $V_{CE} = 400\text{V}$ ,  $V_{GE} = 0/15\text{V}$ ,  $I_C = 50\text{A}$ ,  $R_G=7\Omega$ , Dynamic test circuit in Figure E)

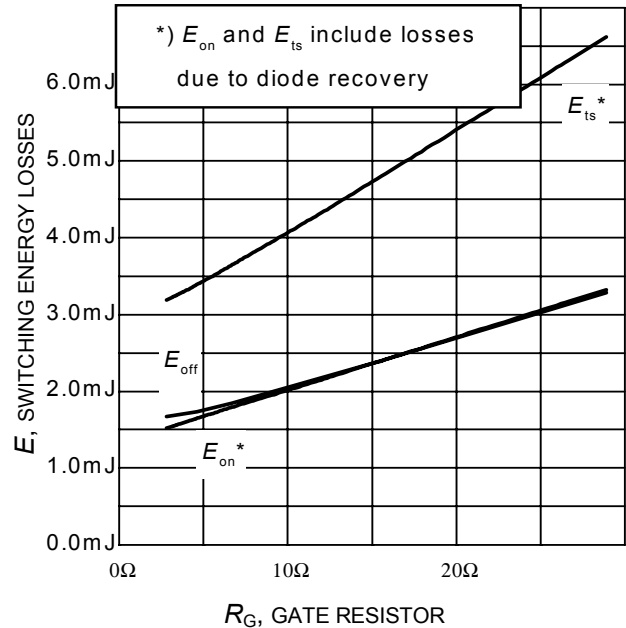


$T_J$ , JUNCTION TEMPERATURE

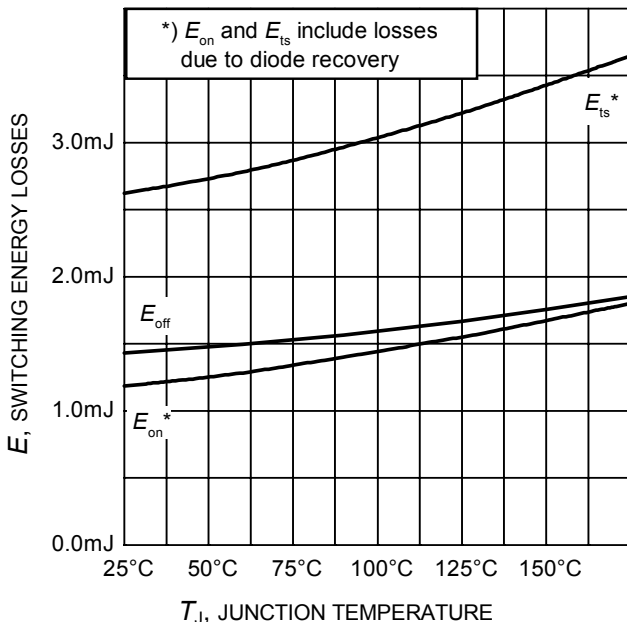
**Figure 12. Gate-emitter threshold voltage as a function of junction temperature**  
( $I_C = 0.8\text{mA}$ )



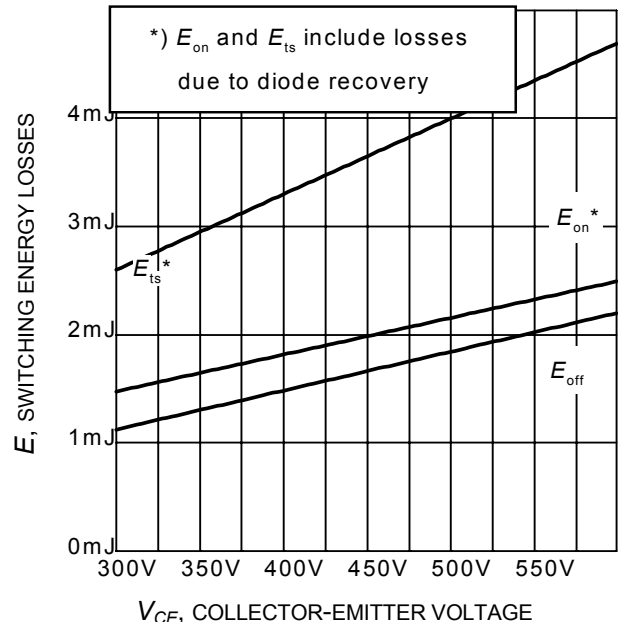
**Figure 13. Typical switching energy losses as a function of collector current**  
(inductive load,  $T_J = 175^\circ\text{C}$ ,  $V_{CE} = 400\text{V}$ ,  $V_{GE} = 0/15\text{V}$ ,  $R_G = 7\Omega$ , Dynamic test circuit in Figure E)



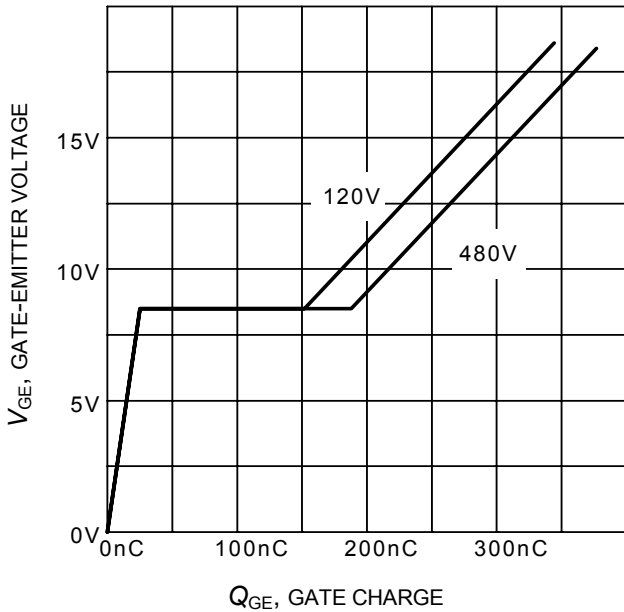
**Figure 14. Typical switching energy losses as a function of gate resistor**  
(inductive load,  $T_J = 175^\circ\text{C}$ ,  $V_{CE} = 400\text{V}$ ,  $V_{GE} = 0/15\text{V}$ ,  $I_C = 50\text{A}$ , Dynamic test circuit in Figure E)



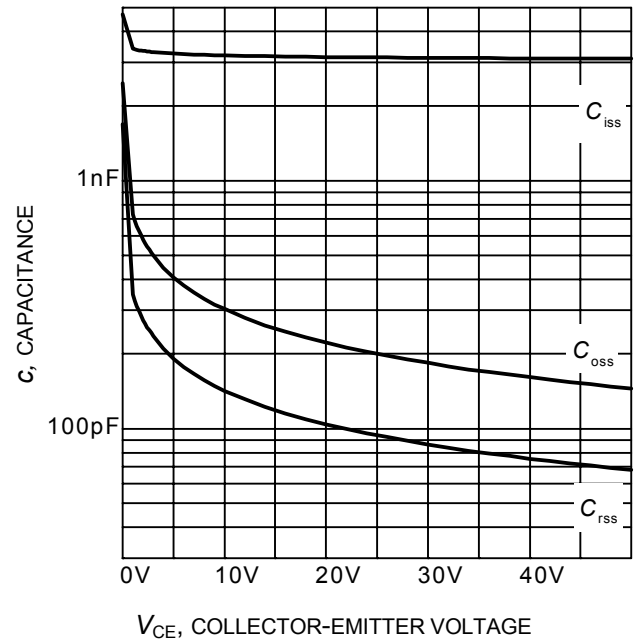
**Figure 15. Typical switching energy losses as a function of junction temperature**  
(inductive load,  $V_{CE} = 400\text{V}$ ,  $V_{GE} = 0/15\text{V}$ ,  $I_C = 50\text{A}$ ,  $R_G = 7\Omega$ , Dynamic test circuit in Figure E)



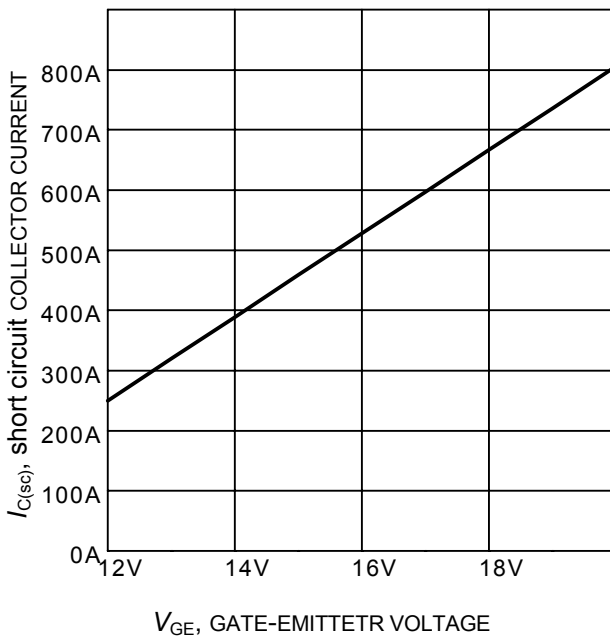
**Figure 16. Typical switching energy losses as a function of collector emitter voltage**  
(inductive load,  $T_J = 175^\circ\text{C}$ ,  $V_{GE} = 0/15\text{V}$ ,  $I_C = 50\text{A}$ ,  $R_G = 7\Omega$ , Dynamic test circuit in Figure E)



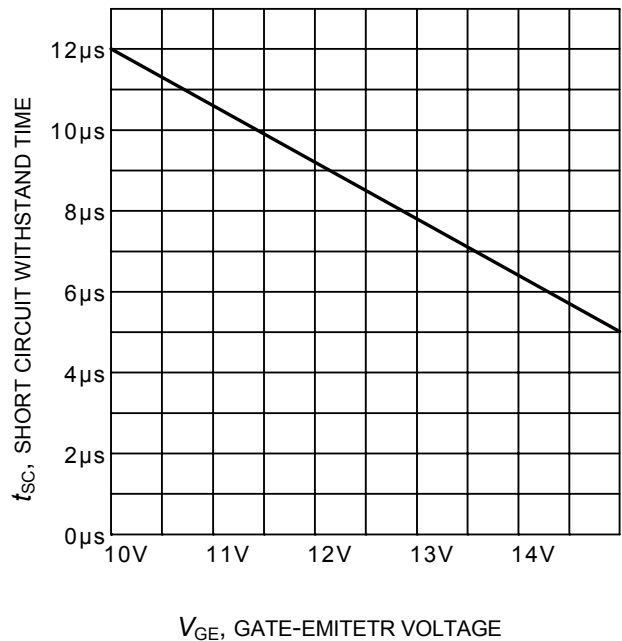
**Figure 17. Typical gate charge**  
( $I_C=50\text{ A}$ )



**Figure 18. Typical capacitance as a function of collector-emitter voltage**  
( $V_{GE}=0\text{V}$ ,  $f = 1\text{ MHz}$ )

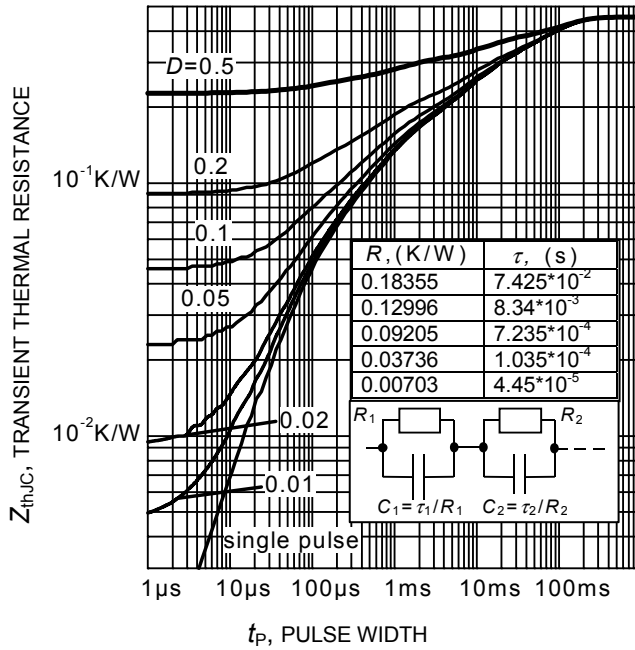


**Figure 19. Typical short circuit collector current as a function of gate-emitter voltage**  
( $V_{CE} \leq 400\text{V}$ ,  $T_j \leq 150^\circ\text{C}$ )



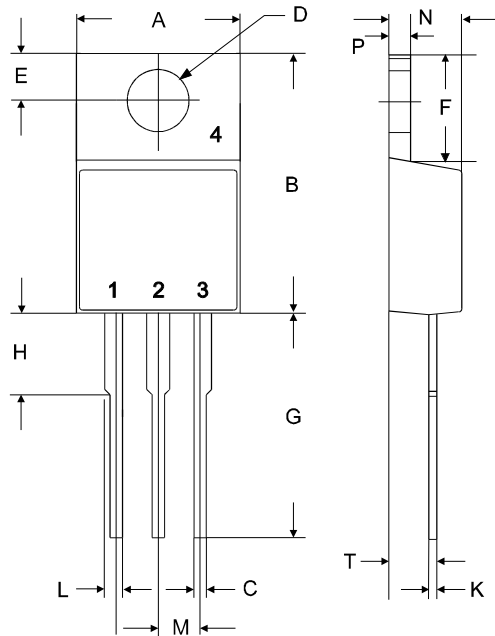
**Figure 20. Short circuit withstand time as a function of gate-emitter voltage**  
( $V_{CE}=600\text{V}$ , start at  $T_j=25^\circ\text{C}$ ,  $T_{jmax}<150^\circ\text{C}$ )





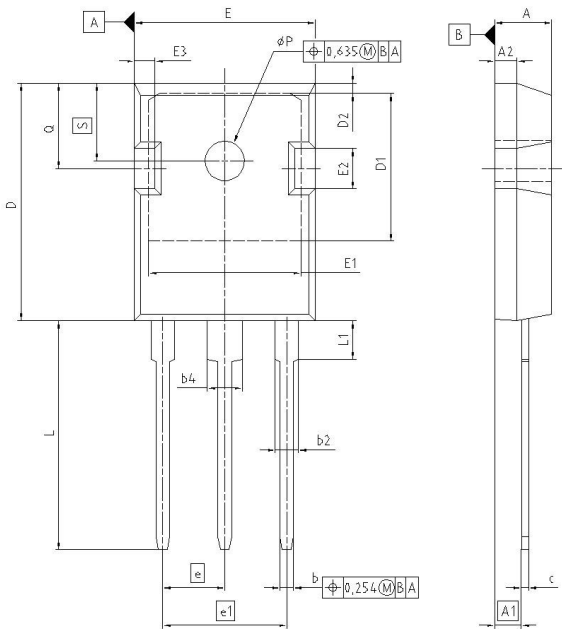
**Figure 21. IGBT transient thermal resistance**  
( $D = t_p / T$ )

PG-TO220-3-1



symbol	Dimensions			
	[mm]		[inch]	
	min	max	min	max
A	9.70	10.30	0.3819	0.4055
B	14.88	15.95	0.5858	0.6280
C	0.65	0.86	0.0256	0.0339
D	3.55	3.89	0.1398	0.1531
E	2.60	3.00	0.1024	0.1181
F	6.00	6.80	0.2362	0.2677
G	13.00	14.00	0.5118	0.5512
H	4.35	4.75	0.1713	0.1870
K	0.38	0.65	0.0150	0.0256
L	0.95	1.32	0.0374	0.0520
M	2.54 typ.		0.1 typ.	
N	4.30	4.50	0.1693	0.1772
P	1.17	1.40	0.0461	0.0551
T	2.30	2.72	0.0906	0.1071

PG-TO247-3-21



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.903	5.157	0.193	0.203
A1	2.273	2.527	0.092	0.096
A2	1.853	2.107	0.075	0.081
b	1.073	1.327	0.047	0.052
b2	1.903	2.386	0.075	0.094
b4	2.870	3.454	0.113	0.136
c	0.549	0.752	0.024	0.030
D	20.823	21.077	0.820	0.830
D1	17.323	17.831	0.682	0.702
D2	1.063	1.317	0.042	0.052
E	15.773	16.027	0.621	0.631
E1	13.893	14.147	0.547	0.557
E2	3.683	3.937	0.145	0.155
E3	1.683	1.937	0.066	0.076
e	5.450		0.215	
e1	10.900		0.430	
N	3		3	
L	20.053	20.307	0.789	0.799
L1	4.168	4.472	0.164	0.176
eP	3.559	3.661	0.140	0.144
Q	5.493	5.747	0.216	0.226
S	6.043	6.297	0.238	0.248

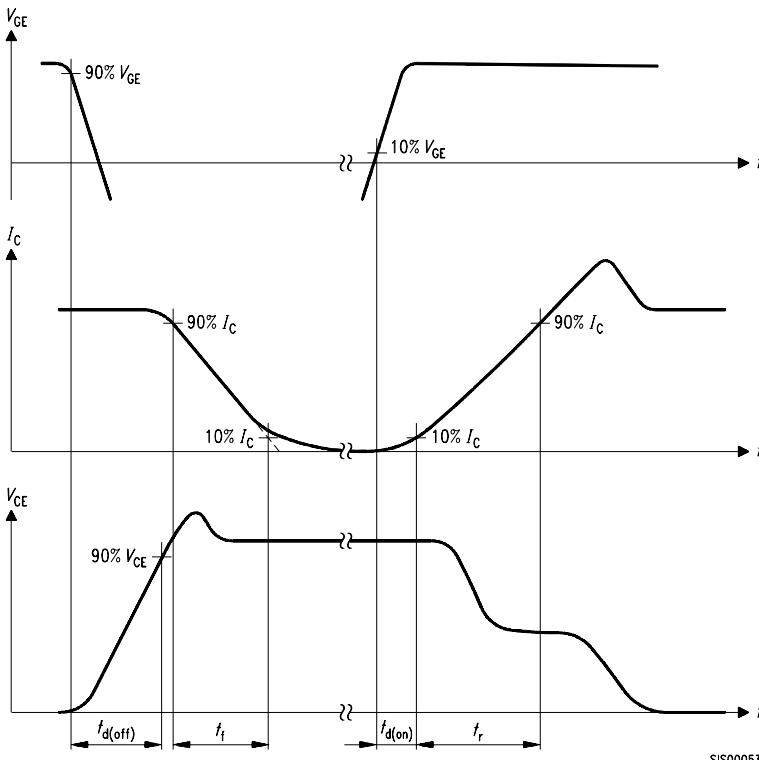


Figure A. Definition of switching times

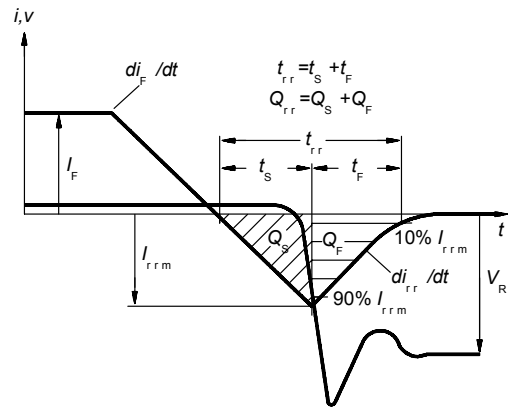


Figure C. Definition of diodes switching characteristics

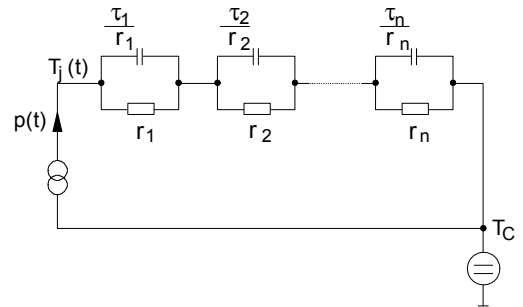


Figure D. Thermal equivalent circuit

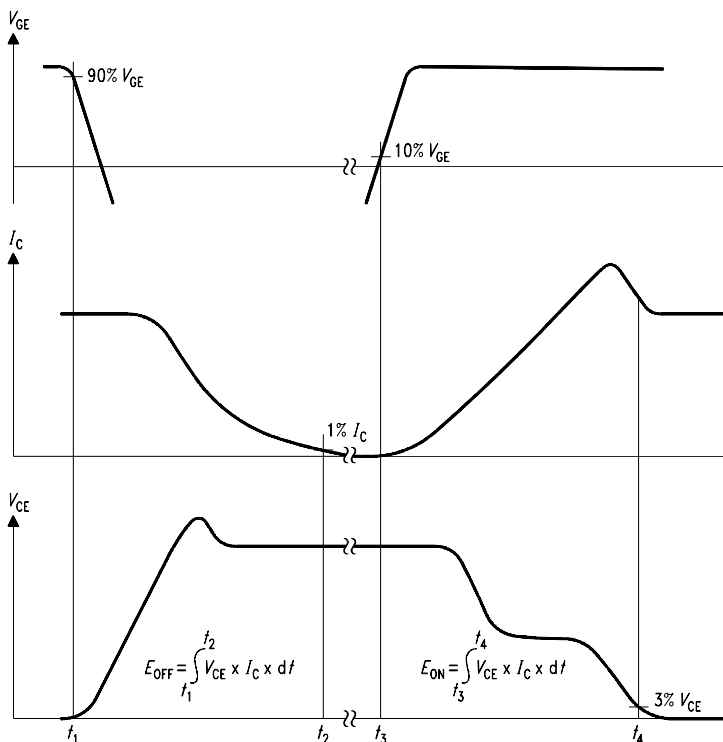


Figure B. Definition of switching losses

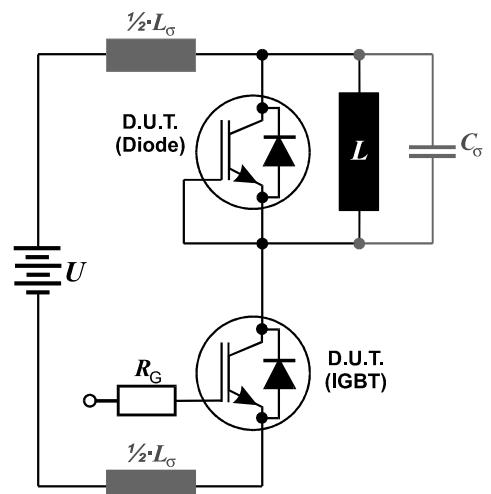


Figure E. Dynamic test circuit

**Edition 2006-01**

**Published by**  
**Infineon Technologies AG**  
**81726 München, Germany**

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